

General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

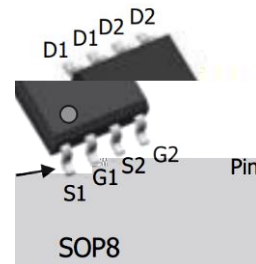
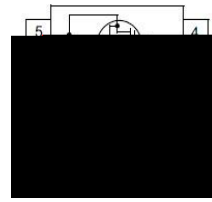
Features

Trench technology
 $R_{DS(ON)}$ to minimize conductive loss

Application

2nd Synchronous Rectifier

Product Summary



Ordering Information:

Part NO.	
Marking	
Packing Information	REEL TAPE
Basic ordering unit (pcs)	4000

Absolute Maximum Ratings $T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	12	A
	$I_{D@TC=75}$	10.6	A
	$I_{D@TC=100}$	8.8	A
Pulsed Drain Current	I_{DM}	42	A
Total Power Dissipation	$P_D@TC=25$	3.1	W
Total Power Dissipation	$P_D@TA=25$	0.69	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	150	mJ

Fig.1 Gate-Charge Characteristics

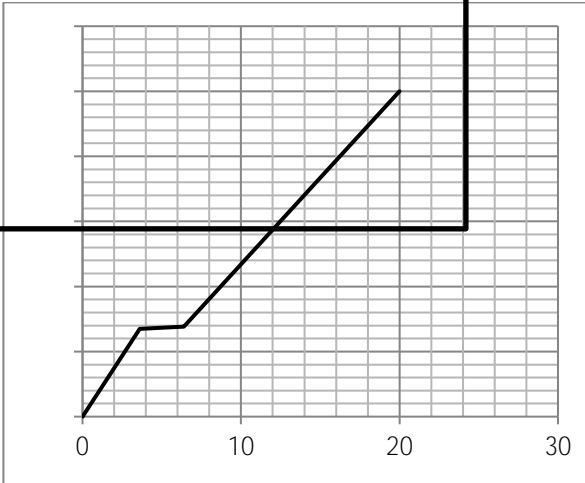


Fig.2 Capacitance Characteristics

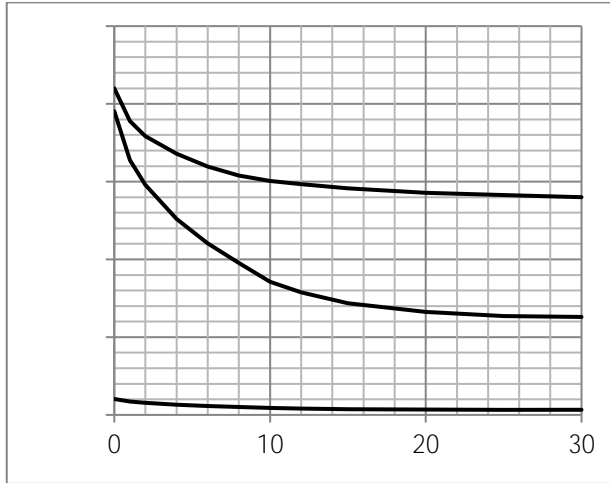


Fig.3 Power Dissipation

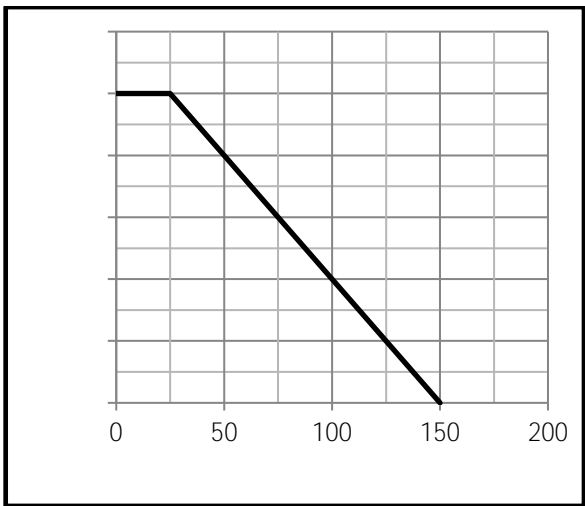


Fig.4 Typical output Characteristics

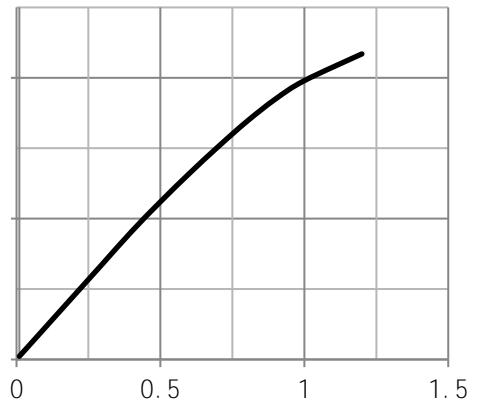


Fig.5 Threshold Voltage V.S Junction Temperature

Fig.6 Resistance V.S Drain Current



Dimensions(SOP8)

Unit: mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.25	C	1.30		1.75
A1	0.37		0.49	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.10	0.20	0.23

B1